

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**PATENT** 

In re application of: O'DONNELL

Application No.: 09/472,757

Filed: December 27, 1999

Title: INSITU POST ETCH PROCESS TO REMOVE REMAINING PHOTORESIST AND RESIDUAL SIDEWALL PASSIVATION

Attorney Docket No.: LAM1P133/P0582

Examiner: Umez Eronini, Lynette T.

Group: 1765

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail to: Box Non-Fee Amendment, Commissioner for Patents, Washington, D.C. 20231 on October 9, 2002.

Signed:

## AMENDMENT C

Box Non-Fee Amendment Commissioner for Patents Washington, D.C. 20231

Dear Madame:

This is in response to the office action mailed July 31, 2002. Please consider the following remarks and amend the above-identified patent application as follows:

## In the Claims:

Please add new claims 19 and 20 and amend claim 17, as follows:

- 17. (Once Amended) The method, as recited in claim 1, wherein the stripping away the etch mask and removing some residual sidewall passivation, simultaneously strips away the etch mask and removes [comprises removing] parts of the metal-containing layer that are redeposited to form residual sidewall passivation.
- 19. (New) The method, as recited in claim 1, wherein the stripping away the etch mask and removing some sidewall passivation comprises removing metal containing parts of the metal-containing layer that are redeposited to form residual sidewall passivation.